

# INA233 High-Side or Low-Side Measurement, Bidirectional Current and Power Monitor With I<sup>2</sup>C-, SMBus-, and PMBus-Compatible Interface

#### 1 Features

- Senses Bus Voltages From 0 V to 36 V
- · High-Side or Low-Side Sensing
- Reports Current, Voltage, and Power
- Integrated Power Accumulator for Energy and Average Power Monitoring
- High Accuracy:
  - 0.1% Gain Error (Max)
  - 10-µV Offset (Max)
- Configurable Averaging Options
- Independent Alert Limits for Current, Bus Voltage, and Power
- 1.8-V Compliant I<sup>2</sup>C, SMBus, PMBus Interface
- 16 Programmable Addresses
- Operates From a 2.7-V to 5.5-V Power Supply
- 10-Pin, DGS (VSSOP) Package

# 2 Applications

- Servers
- Telecom Infrastructure
- High-Performance Computing
- Power Metering
- Battery Chargers
- · Power Supply
- Test Equipment

## 3 Description

The INA233 device is a current, voltage, and power monitor with an I<sup>2</sup>C-, SMBus-, and PMBus-compatible interface that is compliant with digital bus voltages from 1.8 V to 5.0 V. The device monitors and reports values for current, voltage, and power. The integrated power accumulator can be used for energy or average power calculations. Programmable calibration value, conversion times, and averaging when combined with an internal multiplier enable direct readouts of current in amperes and power in watts.

The INA233 senses current on common-mode bus voltages that can vary from 0 V to 36 V, independent of the supply voltage. The device operates from a single 2.7-V to 5.5-V supply, drawing a typical supply current of 310 μA in normal operation. The device can be placed in a low-power standby mode where the typical operating current is only 2 μA. The device is specified over the operating temperature range between -40°C and +125°C and features up to 16 programmable addresses.

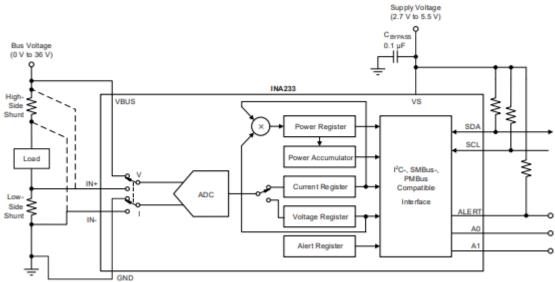
# Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (NOM)
INA233	VSSOP (10)	3.00 mm x 3.00 mm

 For all available packages, see the orderable addendum at the end of the datasheet.

Дктивания V

# High-Side or Low-Side Sensing Application

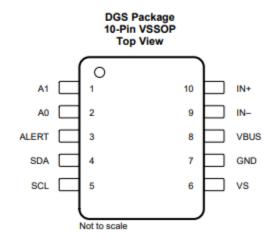


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# 5 Pin Configuration and Functions



#### Pin Functions

	Fill Full Culotis					
	PIN	. VO	DESCRIPTION			
NAME	NO.	100	DESCRIPTION			
A0	2	Digital input	Address pin. Connect to GND, SCL, SDA, or VS. Table 3 lists the pin settings and corresponding addresses.			
A1	1	Digital input	pin. Connect to GND, SCL, SDA, or VS. Table 3 lists the pin settings and corresponding addresses.			
ALERT	3	Digital output	PMBus-compatible multifunctional alert, open-drain output. This pin alerts on independent settings for overcurrent, under- and overvoltage, and overpower conditions.			
GND	7	Analog	Ground			
IN-	9	Analog input	Connect to the load side of the shunt resistor			
IN+	10	Analog input	Connect to the supply side of the shunt resistor	1		
SCL	5	Digital input	Serial bus clock line, open-drain input	1		
SDA	4	Digital I/O	Serial bus data line, open-drain input/output	1		
VBUS	8	Analog input	Bus voltage input			
VS	6	Analog	Power supply, 2.7 V to 5.5 V AКТИВАЦИЯ	V		

# 6 Specifications

#### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V <sub>VS</sub>	Supply voltage			6	V
	Analan Innerta INI. INI	Differential (V <sub>IN+</sub> – V <sub>IN-</sub> ) <sup>(2)</sup>	-40	40	.,
	Analog Inputs, IN+, IN-	Common-mode	-0.3	40	V
V <sub>VBUS</sub>	VBUS pin voltage	·	-0.3	40	V
V <sub>SDA</sub>	SDA, SCL pin voltages		GND - 0.3	6	V
VA	A0, A1 pin voltages		GND - 0.3	6	V
I <sub>IN</sub>	Input current into any pin			5	mA
I <sub>OUT</sub>	Open-drain digital output current			10	mA
TJ	Junction temperature			150	°C
T <sub>stg</sub>	Storage temperature		-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

#### 6.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	±2500	V
V <sub>(ESD)</sub>	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±1000	V

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

<sup>(2)</sup> IN+ and IN- can have a differential voltage between -40 V and 40 V. However, the voltage at these pins must not exceed the range of -0.3 V to 40 V.

<sup>(2)</sup> JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

# 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM MAX	UNIT
V <sub>CM</sub>	Common-mode input voltage	0	36	V
V <sub>VS</sub>	Operating supply voltage	2.7	5.5	V
TA	Operating free-air temperature	-40	125	°C

#### 6.4 Thermal Information

		INA233	
	THERMAL METRIC <sup>(1)</sup>	DGS (VSSOP)	UNIT
		10 PINS	
R <sub>0JA</sub>	Junction-to-ambient thermal resistance	171.4	°C/W
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	42.9	°C/W
R <sub>0JB</sub>	Junction-to-board thermal resistance	91.8	°C/W
ΨЈТ	Junction-to-top characterization parameter	1.5	°C/W
ΨЈВ	Junction-to-board characterization parameter	90.2	°C/W
R <sub>0JC(bot)</sub>	Junction-to-case (bottom) thermal resistance	n/a	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

# **Electrical Characteristics (continued)**

at  $T_A = 25^{\circ}C$ ,  $V_{VS} = 3.3 \text{ V}$ ,  $V_{IN+} = 12 \text{ V}$ ,  $V_{SENSE} = (V_{IN+} - V_{IN-}) = 0 \text{ mV}$ , and  $V_{VBUS} = 12 \text{ V}$  (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
DIGITAL	INPUT/OUTPUT					
	Input capacitance			3		pF
	Leakage input current	$0 \ V \le V_{SCL} \le V_{VS}$ , $0 \ V \le V_{SDA} \le V_{VS}$ , $0 \ V \le V_{Alert} \le V_{VS}$ , $0 \ V \le V_{A0} \le V_{VS}$ , $0 \ V \le V_{A1} \le V_{VS}$		0.5	2	μА
V <sub>IH</sub>	High-level input voltage	SDA pin	1.4		6	V
V <sub>IL</sub>	Low-level input voltage	SDA pin	-0.3		0.4	V
V <sub>OL</sub>	Low-level output voltage	I <sub>OL</sub> = 3 mA, SDA and ALERT pins	0		0.4	V
	Hysteresis			500		mV
POWER	SUPPLY	•				
	Operating supply range		2.7		5.5	V
l <sub>a</sub>	Quiescent current			310	400	μА
	Quiescent current, power-down (shutdown) mode			2	5	μА
V <sub>POR</sub>	Power-on-reset (POR) threshold voltage			2		٧

# 6.5 Electrical Characteristics

at  $T_A = 25$ °C,  $V_{VS} = 3.3$  V,  $V_{IN+} = 12$  V,  $V_{SENSE} = (V_{IN+} - V_{IN-}) = 0$  mV, and  $V_{VBUS} = 12$  V (unless otherwise noted)

A	0 0, 1VS 0.0 1, 1N1 12 1, 1SENSI	E (*IN+ *IN-/ **IN-/ **IN-/ **IN-/	12 1 (4111000 04110	minos motosa/	
	PARAMETER	TEST CONDITIONS	MIN T	YP MAX	UNIT
INPUT					
	Shunt voltage input range		-81.92	81.9175	mV
	Bus voltage input range (1)		0	36	V
CMRR	Common-mode rejection ratio	0 V ≤ V <sub>IN+</sub> ≤ 36 V	126	140	dB
.,	0.7	Shunt voltage	±	2.5 ±10	μV
Vos	Offset voltage, RTI <sup>(2)</sup>	Bus voltage	±1	.25 ±7.5	mV
	(27)	Shunt voltage, –40°C ≤ T <sub>A</sub> ≤ +125°C	0	0.02 0.1	
	V <sub>OS</sub> (RTI <sup>(2)</sup> ) vs temperature	Bus voltage, -40°C ≤ T <sub>A</sub> ≤ +125°C		10 40	μV/°C
D0DD	D (1.17)	Shunt voltage, 2.7 V ≤ V <sub>S</sub> ≤ 5.5 V		1	μV/V
PSRR	Power-supply rejection ratio (RTI <sup>(2)</sup> )	Bus voltage		0.5	mV/V
I <sub>B</sub>	Input bias current (I <sub>IN+</sub> , I <sub>IN-</sub> pins)			8	μА
	VBUS input impedance			830	kΩ
	Input leakage <sup>(3)</sup>	(IN+) + (IN-), power-down mode		0.1 0.5	μА
DC ACC	JRACY				•
	ADC native resolution			16	Bits
		Shunt voltage		2.5	μV
	1-LSB step size	Bus voltage	1	.25	mV
	Shunt voltage gain error		0.0	2% 0.1%	
	Shunt voltage gain error vs temperature	-40°C ≤ T <sub>A</sub> ≤ +125°C		5 25	ppm/°C
	Bus voltage gain error		0.0	2% 0.1%	
	Bus voltage gain error vs temperature	-40°C ≤ T <sub>A</sub> ≤ +125°C		10 50	ppm/°C
	Power gain error	$V_{BUS} = 12 \text{ V}, V_{IN+} - V_{IN-} = -80 \text{ mV}$ to 80 mV	0.0	5% 0.2%	
	Power gain error vs temperature	-40°C ≤ T <sub>A</sub> ≤ +125°C		10 50	ppm/°C
DNL	Differential nonlinearity		±	:0.1	LSB
	,	CT bit = 000		140 154	
		CT bit = 001		204 224	1
		CT bit = 010	:	332 365	μs
		CT bit = 011		588 646	1
t <sub>CT</sub>	ADC conversion time	CT bit = 100		1.1 1.21	
		CT bit = 101	2.	116 <sub>^</sub> 2.328	
		CT bit = 110	4.	156 4.572	ва <b>щ</b> яля
		CT bit = 111	8.3	244 9.068	активи
SMBus					метры".
	SMBus timeout <sup>(4)</sup>			28 35	ms
		I			

<sup>(1)</sup> Although the input range is 36 V, the full-scale range of the ADC scaling is 40.96 V; see the High-Accuracy Analog-to-Digital Convertor (ADC) section. Do not apply more than 36 V.
(2) RTI = Referred-to-input.

<sup>(3)</sup> Input leakage is positive (current flowing into the pin) for the conditions shown at the top of this table. Negative leakage currents can occur under different input conditions.

<sup>(4)</sup> SMBus timeout in the INA233 resets the interface whenever SCL is low for more than 28 ms.